

P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _A = +25°C
-25V	40mΩ @ V _{GS} = -4.5V	-5.4A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Management
- Load Switch
- Battery Protection

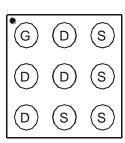
Features and Benefits

- Low Q_g & Q_{gd}
- Small Footprint 1.5mm x 1.5mm
- Gate ESD Protection <HBM Class 3A>
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

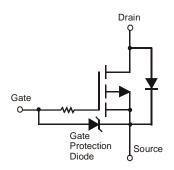
Mechanical Data

- Case: U-WLB1515-9 (Type E)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal: Finish SnAgCu. Solderable per MIL-STD-202 Method 208 @1
- Terminal Connections: See Diagram Below
- · Weight: 0.0018 grams (Approximate)





Top View Pin Configuration



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2541UCB9-7	U-WLB1515-9 (Type E)	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



3D = Product Type Marking Code YM = Date Code Marking Y = Year (ex: F = 2018) M = Month (ex: 9 = September)

Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021
Code	С	D	E	F	G	Н	[

Mon	th	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Cod	le	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	-25	V	
Gate-Source Voltage		V _{GSS}	-6	V	
Continuous Drain Current (Note 5) V _{GS} = -4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	-3.9 -3.1	А
Continuous Drain Current (Note 6) V _{GS} = -4.5V	I _D	-5.4 -4.3	А		
Pulsed Drain Current (Pulse Duration 10µs, Duty C	ycle ≤1%)	I _{DM}	-35	Α	
Continuous Source Pin Current (Note 6)		Is	-1.9	A	
Pulsed Source Pin Current (Pulse Duration 10µs, D	Outy Cycle	I _{SM}	-35	А	

Thermal Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

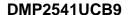
Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_{D}	0.94	W
Total Power Dissipation (Note 6)	P _D	1.78	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ hetaJA}$	135	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ heta JA}$	71	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 7)	OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	-25	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$		
Zero Gate Voltage Drain Current @T _C = +25°C	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -20V, V_{GS} = 0V$		
Gate-Source Leakage	I _{GSS}	_	_	-100	nA	$V_{GS} = -6V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage	V _{GS(TH)}	-0.4	-0.78	-1.1	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$		
			28	40		$V_{GS} = -4.5V, I_{D} = -2A$		
Static Drain-Source On-Resistance	R _{DS(ON)}	_	36	50	mΩ	$V_{GS} = -2.5V, I_D = -2A$		
	, ,		51	60		V _{GS} = -1.8V, I _D = -2A		
Diode Forward Voltage (Note 5)	V _{SD}	_	-0.74	-1	V	$V_{GS} = 0V, I_{S} = -2A$		
Reverse Recovery Charge	Q _{RR}	_	6.8	_	nC	$V_{DD} = -9.5V$, $I_F = -2A$, $di/dt =$		
Reverse Recovery Time	t _{RR}	_	13.6	_	ns	200A/µs		
DYNAMIC CHARACTERISTICS (Note 8)		•	•	•	•			
Input Capacitance	C _{iss}	_	566	850	pF	10/1/		
Output Capacitance	Coss	_	343	515	pF	$V_{DS} = -10V, V_{GS} = 0V,$ - f = 1.0MHz		
Reverse Transfer Capacitance	C_{rss}	_	20	30	pF	1 = 1.000112		
Series Gate Resistance	Rg	_	12.1	18	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$		
Total Gate Charge	Qq	_	4.7	7	nC			
Gate-Source Charge	Qgs	_	0.6	_	nC	$V_{GS} = -4.5V, V_{DS} = -10V,$		
Gate-Drain Charge	Q _{gd}	_	1.0	_	nC	$I_D = -2A$		
Turn-On Delay Time	t _{D(ON)}	_	3.4	6.8	ns			
Turn-On Rise Time	t _R	_	6.5	_	ns	$V_{DD} = -10V, V_{GS} = -4.5V,$		
Turn-Off Delay Time	t _{D(OFF)}	_	55	110	ns	$I_{DS} = -2A$, $R_g = 2\Omega$		
Turn-Off Fall Time	t _F	_	43	_	ns	7		

Notes:

- Device mounted on FR-4 PCB with minimum recommended pad layout.
 Device mounted on FR-4 material with 1inch² (6.45cm²), 2oz. (0.071mm thick) Cu.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.





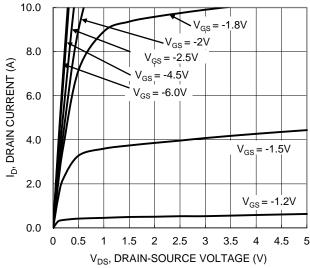


Figure 1. Typical Output Characteristic

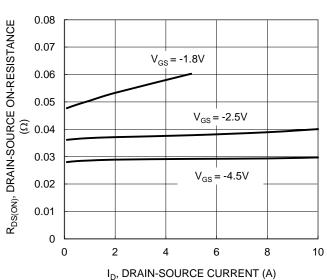


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

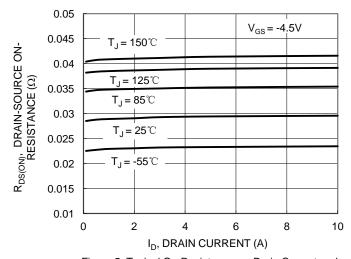


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

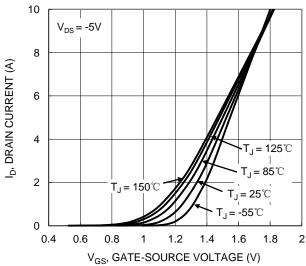
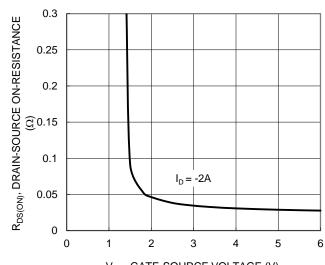


Figure 2. Typical Transfer Characteristic



V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 4. Typical Transfer Characteristic

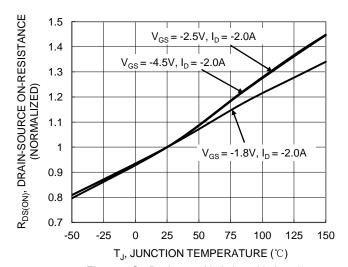


Figure 6. On-Resistance Variation with Junction Temperature



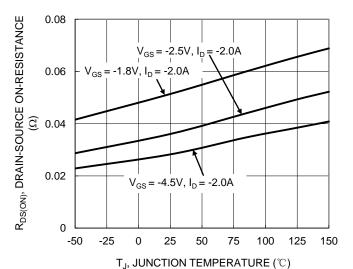


Figure 7. On-Resistance Variation with Junction Temperature

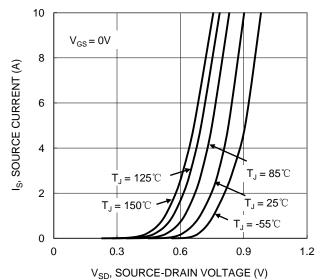


Figure 9. Diode Forward Voltage vs. Current

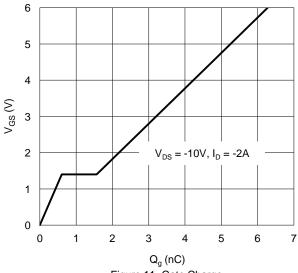


Figure 11. Gate Charge

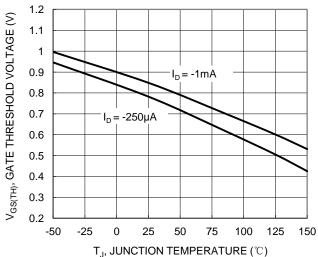


Figure 8. Gate Threshold Variation vs. Junction Temperature

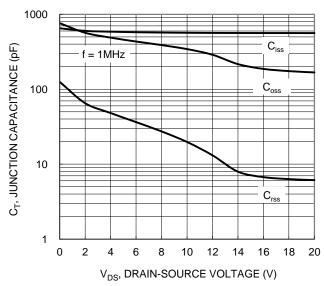


Figure 10. Typical Junction Capacitance

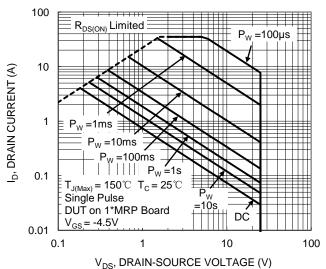


Figure 12. SOA, Safe Operation Area



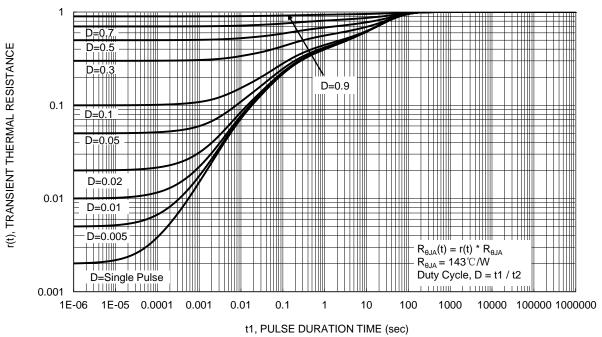


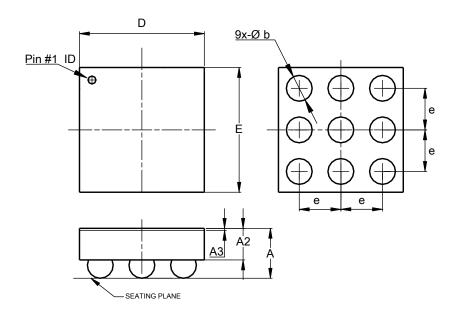
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-WLB1515-9 (Type E)

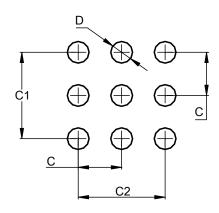


U-WLB1515-9 (Type E)								
Dim	Dim Min Max Typ							
Α		0.62						
A2		0.36	0.36					
A3	0.020	0.030	0.025					
b	0.27	0.37	0.32					
D	1.47	1.51	1.49					
Е	1.47	1.51	1.49					
е	0.50							
All Dimensions in mm								

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-WLB1515-9 (Type E)



Dimensions	Value (in mm)
С	0.50
C1	1.00
C2	1.00
D	0.25



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